



ST3237E

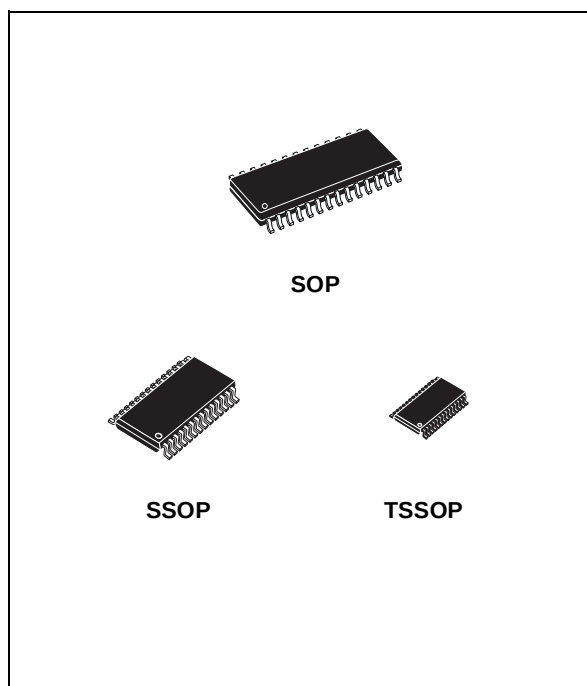
±15KV ESD-PROTECTED, 1μA, 3 TO 5.5V, 250KBPS, RS-232 TRANSCEIVER WITH STAND-BY

- EDS PROTECTION FOR RS-232 I/O PINS:
±15KV HUMAN BODY MODEL
±8KV IEC 1000-4-2 CONTACT DISCHARGE
- 1μA LOW POWER SHUTDOWN WITH
RECEIVERS ACTIVE
- GUARENTEED DATA RATE
250Kbps (Normal Operation)
1Mbps (Very High Speed Operation)
- GUARANTEED SLEW RATE RANGE
6V/μs (Normal Operation)
24V/μs (Very High Speed Operation)
- 0.1μF EXTERNAL CAPACITORS
- FLOW-THROUGH PINOUT
- AVAILABLE IN SO-28, SSOP-28 AND
TSSOP28
- LOW SUPPLY CURRENT 300μA

DESCRIPTION

The ST3237E is a 3V to 5.5V powered EIA/ TIA-232 and V.28/V.24 communication interfaces high data-rate capability and enhanced electrostatic discharge (ESD) protection at ±8KV using IEC1000-4-2 contact discharge and ±15kV using Human Body Model (HBM). The other pins are protected with standard ESD protection at ±2kV using HBM method. The ST3237C is a transceiver (5 drivers, 3 receivers) for fast modem applications.

The device has a proprietary low-dropout transmitter output stage providing true RS-232



performance from a 3V to 5.5V supply using a dual charge pump. The device is guaranteed to run at data rates of 250Kbps in the normal operation mode and 1Mbps in the very high speed operation mode while maintaining RS-232 output levels.

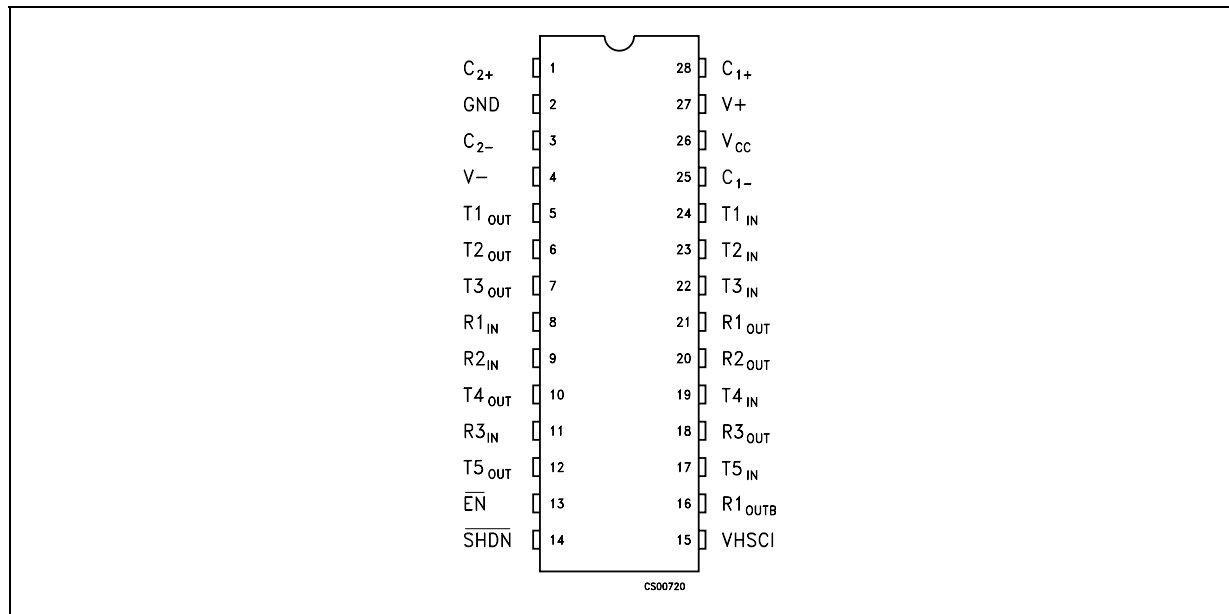
ORDERING CODES

Type	Temperature Range	Package	Comments
ST3237ECD	0 to 70 °C	SO-28 (Tube)	27parts per tube / 12tube per box
ST3237EBD	-40 to 85 °C	SO-28 (Tube)	27parts per tube / 12tube per box
ST3237ECDR	0 to 70 °C	SO-28 (Tape & Reel)	1000 parts per reel
ST3237EBDR	-40 to 85 °C	SO-28 (Tape & Reel)	1000 parts per reel
ST3237ECPR	0 to 70 °C	SSOP-28 (Tape & Reel)	1350 parts per reel
ST3237EBPR	-40 to 85 °C	SSOP-28 (Tape & Reel)	1350 parts per reel
ST3237ECTR (*)	0 to 70 °C	TSSOP28 (Tape & Reel)	2500 parts per reel
ST3237EBTR	-40 to 85 °C	TSSOP28 (Tape & Reel)	2500 parts per reel

PIN DESCRIPTION

PIN N°	SYMBOL	NAME AND FUNCTION
1	C ₂ ⁺	Positive Terminal of Inverting Charge Pump Capacitor
2	GND	Ground
3	C ₂ ⁻	Negative Terminal of Inverting Charge Pump Capacitor
4	V ⁻	-5.5V Generated by the Charge Pump
5	T ₁ _{OUT}	First Transmitter Output Voltage
6	T ₂ _{OUT}	Second Transmitter Output Voltage
7	T ₃ _{OUT}	Third Transmitter Output Voltage
8	R ₁ _{IN}	First Receiver Input Voltage
9	R ₂ _{IN}	Second Receiver Input Voltage
10	T ₄ _{OUT}	Fourth Transmitter Output Voltage
11	R ₃ _{IN}	Third Receiver Input Voltage
12	T ₅ _{OUT}	Fifth Transmitter Output Voltage
13	EN	Receiver Enable, Active Low
14	SHDN	Shutdown Control, Active Low
15	VHSCI	Very High Speed Control Input. Connected to GND for normal operation; connected to VCC for 1Mbps transmission rates.
16	R ₁ _{OUTB}	Non Inverting Complementary Receiver Output. Always Active.
17	T ₅ _{IN}	Fifth Transmitter Input Voltage
18	R ₃ _{OUT}	Third Receiver Output Voltage
19	T ₄ _{IN}	Fourth Transmitter Input Voltage
20	R ₂ _{OUT}	Second Receiver Output Voltage
21	R ₁ _{OUT}	First Receiver Output Voltage
22	T ₃ _{IN}	Third Transmitter Input Voltage
23	T ₂ _{IN}	Second Transmitter Input Voltage
24	T ₁ _N	First Transmitter Input Voltage
25	C ₁ ⁻	Negative Terminal of Voltage-Doubler Charge Pump Capacitor
26	V _{CC}	Supply Voltage
27	V ⁺	5.5V Generated by the Charge Pump
28	C ₁ ⁺	Positive Terminal of Voltage-Doubler Charge Pump Capacitor

PIN CONFIGURATION



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.3 to 6	V
V+	Doubled Voltage Terminal	-0.3 to 7	V
V-	Inverted Voltage Terminal	0.3 to -7	V
$V+ + V- $		13	V
T_{IN}	Transmitter Input Voltage Range	-0.3 to 6	V
SHDN, EN		-0.3 to 6	V
VHSCI	Very High Speed Control Input	-0.3 to ($V_{CC} + 0.3$)	V
R_{IN}	Receiver Input Voltage Range	± 25	V
T_{OUT}	Transmitter Output Voltage Range	± 13.2	V
R_{OUT}, R_{OUTB}	Receiver Output Voltage Range	-0.3 to ($V_{CC} + 0.3$)	V
t_{SHORT}	Short Circuit Duration on T_{OUT} (one at a time)	Continuous	
T_{stg}	Storage Temperature Range	-65 to 150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied. V+ and V- can have a maximum magnitude of +7V, but their absolute addition can not exceed 13 V.

SHUTDOWN AND ENABLE CONTROL TRUTH TABLE

SHDN	EN	T-OUT	R-OUT	R-OUTB
0	0	High Z	Active	Active
0	1	High Z	High Z	Active
1	0	Active	Active	Active
1	1	Active	High Z	Active

ESD PERFORMANCE: TRANSMITTER OUTPUTS, RECEIVER INPUTS

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
ESD	ESD Protection Voltage	Human Body Model	±15			kV
ESD	ESD Protection Voltage	IEC-1000-4-2 Contact Discharge	±8			kV

ELECTRICAL CHARACTERISTICS

($C_1 - C_4 = 0.1\mu\text{F}$, $V_{CC} = 3\text{V}$ to 5.5V , $T_A = -40$ to 85°C , unless otherwise specified.

Typical values are referred to $T_A = 25^\circ\text{C}$)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SUPPLY}	V_{CC} Power Supply Current	SHDN= V_{CC} No Load		0.3	1	mA
I_{SHDN}	Shutdown Supply Current	SHDN=GND V_{T_IN} =GND or V_{CC}		1	5	μA

LOGIC INPUT ELECTRICAL CHARACTERISTICS

($C_1 - C_4 = 0.1\mu\text{F}$, $V_{CC} = 3\text{V}$ to 5.5V , $T_A = -40$ to 85°C , unless otherwise specified.

Typical values are referred to $T_A = 25^\circ\text{C}$)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_{TIL}	Input Logic Threshold Low (Note 1)	T-IN, VHSCI, EN, SHDN			0.8	V
V_{TIH}	Input Logic Threshold High	T-IN, VHSCI, EN, SHDN $V_{CC} = 3.3\text{V}$	2			V
		$V_{CC} = 5\text{V}$	2.4			
I_{IL}	Input Leakage Current	T-IN, VHSCI, EN, SHDN			± 1.0	μA
V_{HYS}	Transmitter Input Hysteresis			0.25		V

Note 1: Transmitter input hysteresis is typically 250mV

TRANSMITTER ELECTRICAL CHARACTERISTICS

($C_1 - C_4 = 0.1\mu\text{F}$ tested at $3.3\text{V} \pm 10\%$, $V_{CC} = 3\text{V}$ to 5.5V , $T_A = -40$ to 85°C , unless otherwise specified.

Typical values are referred to $T_A = 25^\circ\text{C}$)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_{TOUT}	Output Voltage Swing	All Transmitter outputs are loaded with $3\text{K}\Omega$ to GND	± 5	± 5.4		V
R_{TOUT}	Transmitter Output Resistance	$V_{CC} = 0\text{V}$ $V_{\text{OUT}} = \pm 2\text{V}$	300	10M		Ω
I_{SC}	Output Short Circuit Current			± 60		mA
I_{TOL}	Output Leakage Current	$V_{CC} = 0\text{V}$ or 3.3V to 5.5V $V_{\text{OUT}} = \pm 12\text{V}$ Transmitters Disable			± 25	μA

RECEIVER ELECTRICAL CHARACTERISTICS

($C_1 - C_4 = 0.1\mu\text{F}$ tested at $3.3\text{V} \pm 10\%$, $V_{\text{CC}} = 3\text{V}$ to 5.5V , $T_A = -40$ to 85°C , unless otherwise specified. Typical values are referred to $T_A = 25^\circ\text{C}$)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{OL}	Output Leakage Current	Receiver Disabled $\overline{\text{EN}} = V_{\text{CC}}$		± 0.05	± 10	μA
V_{OL}	Output Voltage Low	$I_{\text{OUT}} = 1\text{mA}$			0.4	V
V_{OH}	Output Voltage High	$I_{\text{OUT}} = -1\text{mA}$	$V_{\text{CC}} - 0.6$	$V_{\text{CC}} - 0.1$		V
V_{RIN}	Receiver Input Voltage Operating Range		-25		25	V
V_{RIL}	RS-232 Input Threshold Low	$T_A = 25^\circ\text{C}$ $V_{\text{CC}} = 3.3\text{V}$	0.6	1.1		V
		$T_A = 25^\circ\text{C}$ $V_{\text{CC}} = 5\text{V}$	0.8	1.5		
V_{RIH}	RS-232 Input Threshold High	$T_A = 25^\circ\text{C}$ $V_{\text{CC}} = 3.3\text{V}$		1.5	2.4	V
		$T_A = 25^\circ\text{C}$ $V_{\text{CC}} = 5\text{V}$		1.2	2.4	
V_{RIHYS}	Input Hysteresis			0.3		V
R_{RIN}	Input Resistance	$T_A = 25^\circ\text{C}$	3	5	7	$\text{K}\Omega$

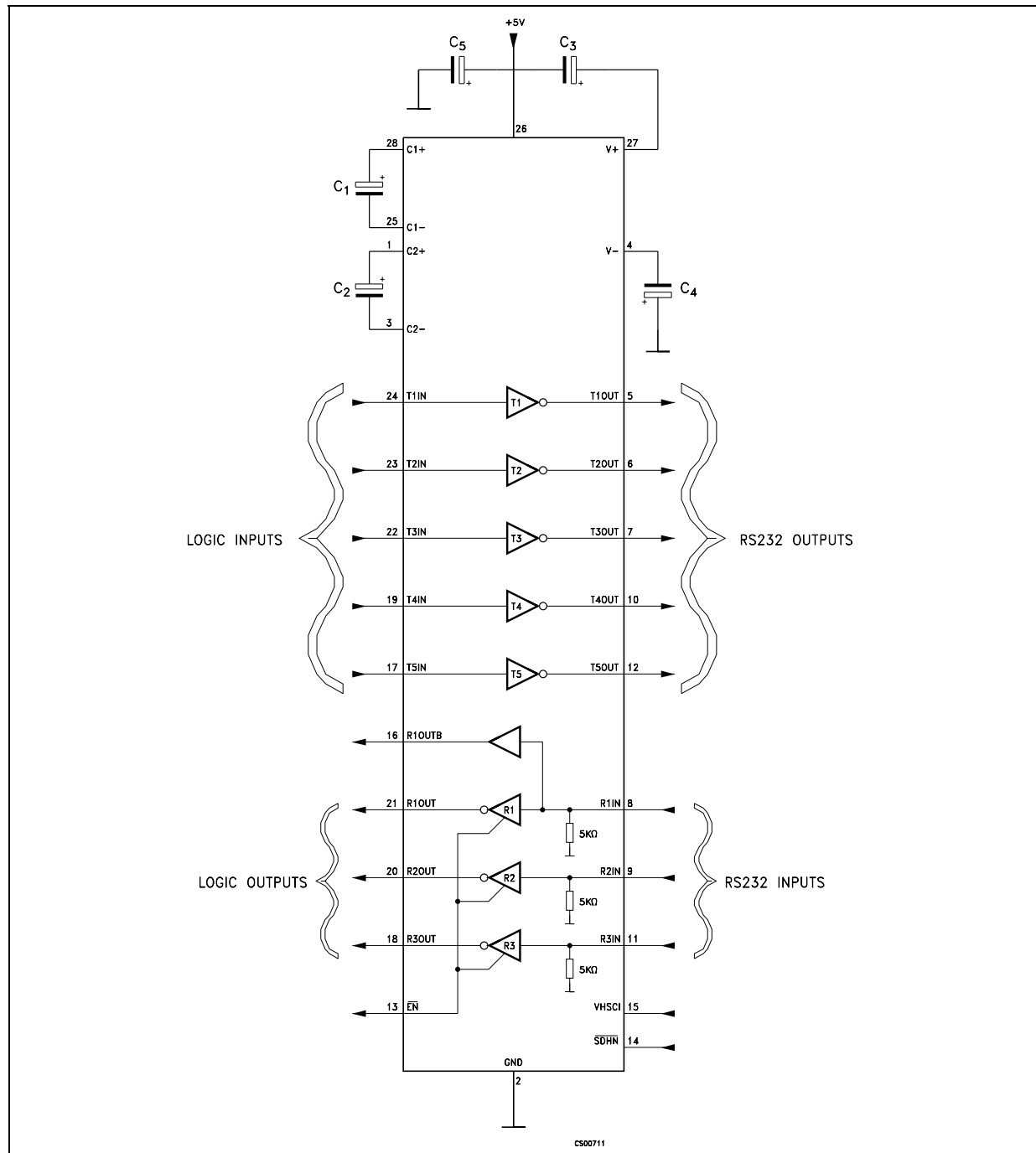
TIMING CHARACTERISTICS

($C_1 - C_4 = 0.1\mu\text{F}$ tested at $3.3\text{V} \pm 10\%$, $V_{\text{CC}} = 3\text{V}$ to 5.5V , $T_A = -40$ to 85°C , unless otherwise specified. Typical values are referred to $T_A = 25^\circ\text{C}$)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
D_R	Maximum Data Rate	$R_L = 3\text{K}\Omega$ $C_L = 1000\text{pF}$ one transmitter switching $\text{VHSCI} = \text{GND}$	250			Kbps
		$R_L = 3\text{K}\Omega$ $C_L = 250\text{pF}$ one transmitter switching $\text{VHSCI} = V_{\text{CC}}$ $V_{\text{CC}} = 3$ to 4.5V	1000			Kbps
		$R_L = 3\text{K}\Omega$ $C_L = 1000\text{pF}$ one transmitter switching $\text{VHSCI} = V_{\text{CC}}$ $V_{\text{CC}} = 4.5$ to 5.5V	1000			Kbps
t_{PHLR} t_{PLHR}	Propagation Delay Input to Output	R_{IN} to R_{OUT} $C_L = 150\text{pF}$		0.15		μs
t_{PHLR} t_{PLHR}	Propagation Delay Input to Output	$R_L = 3\text{k}\Omega$ $C_L = 1000\text{pF}$ $\text{VHSCI} = V_{\text{CC}}$ $\text{VHSCI} = \text{GND}$		400 1000		ns ns
$t_{\text{T_SKEW}}$	Transmitter Skew	$ t_{\text{PHL}} - t_{\text{TLH}} $ $\text{VHSCI} = \text{GND}$		300		ns
		$ t_{\text{PHL}} - t_{\text{TLH}} $ $\text{VHSCI} = V_{\text{CC}}$		50		ns
$t_{\text{R_SKEW}}$	Receiver Skew	$ t_{\text{PHL}} - t_{\text{TLH}} $		100		ns
t_{OER}	Receiver Output Enable Time	Normal Operation		50		ns
t_{ODR}	Receiver Output Disable Time	Normal Operation		120		ns
S_{RT}	Transition Slew Rate	$T_A = 25^\circ\text{C}$ $R_L = 3$ to $7\text{K}\Omega$ $V_{\text{CC}} = 3.3\text{V}$ measured from $+3\text{V}$ to -3V or -3V to $+3\text{V}$				$\text{V}/\mu\text{s}$ $\text{V}/\mu\text{s}$ $\text{V}/\mu\text{s}$
		$C_L = 150\text{pF}$ to 1000pF $\text{VHSCI} = \text{GND}$	6		30	
		$C_L = 150\text{pF}$ to 1000pF $\text{VHSCI} = V_{\text{CC}}$	24		150	
		$C_L = 150\text{pF}$ to 2500pF $\text{VHSCI} = \text{GND}$	4		30	

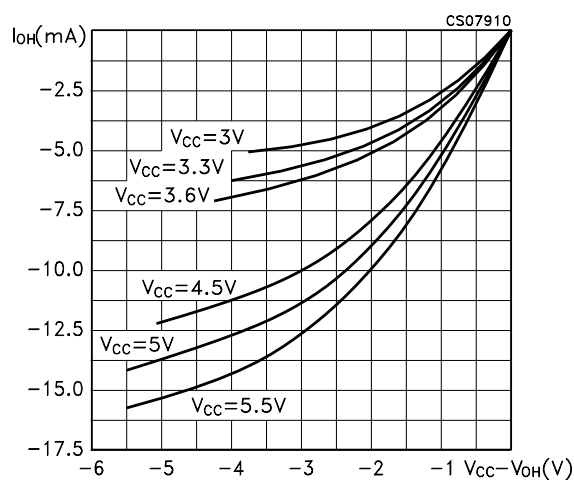
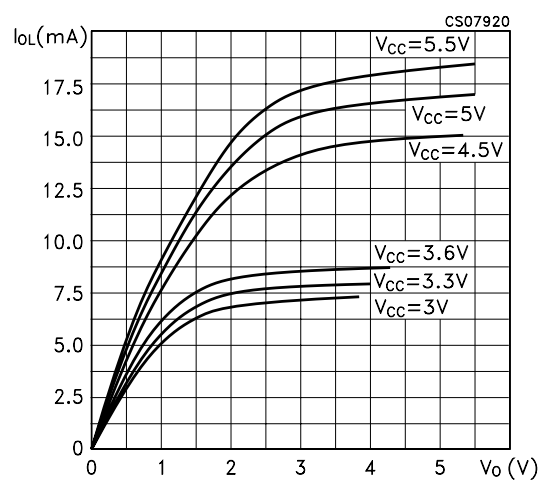
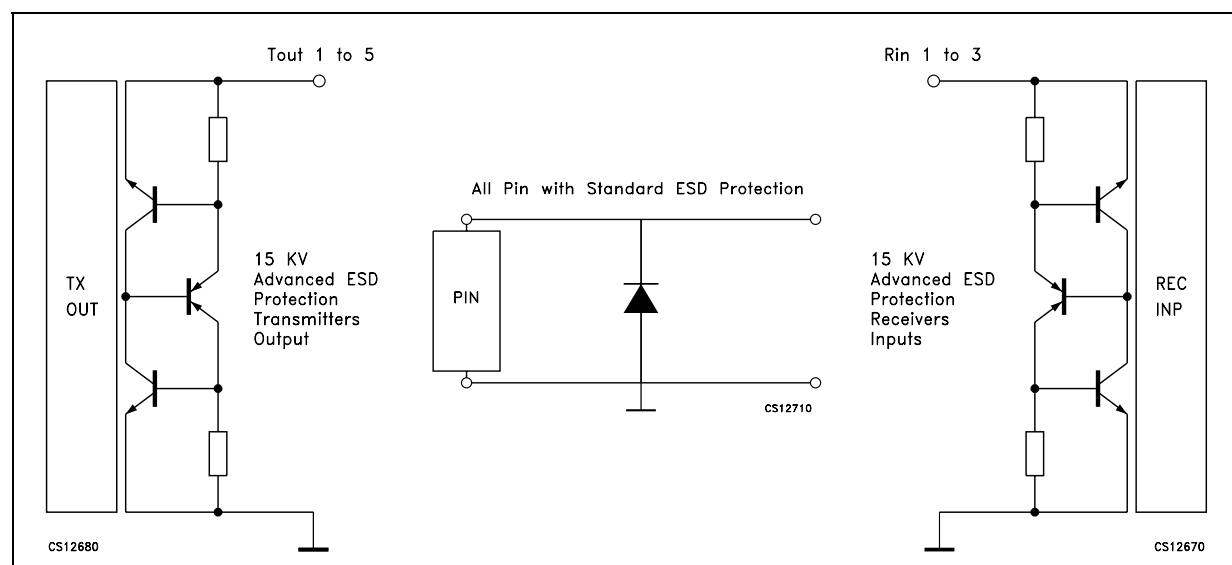
Transmitter Skew is measured at the transmitter zero cross points

APPLICATION CIRCUITS

CAPACITANCE VALUE (μF)

V_{CC}	C1	C2	C3	C4	Cbypass
3.0 to 3.6	0.22	0.22	0.22	0.22	0.1
3.1 to 3.6	0.1	0.1	0.1	0.1	0.1
4.5 to 5.5	0.047	0.33	0.33	0.33	0.1
3.0 to 5.5	0.22	0.1	0.1	0.1	0.1

TYPICAL PERFORMANCE CHARACTERISTICS (unless otherwise specified $T_j = 25^\circ\text{C}$)

Figure 1 : LOW Level Receiver Output Current

Figure 2 : HIGH Level Receiver Output Current

ESD PROTECTION


Note: The High ESD protected pins are the I/O RS232 line, transmitter out and receiver in. The other pins guarantee $\pm 2\text{KV}$ HBM ESD protection versus ground by means of diodes.

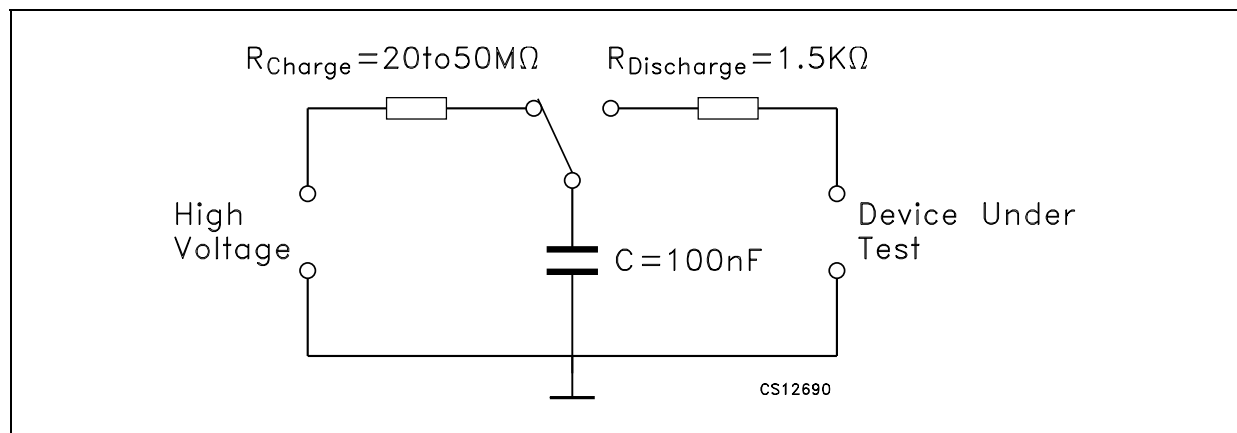
APPLICATION NOTE

This application note describes the procedure for determining the susceptibility and the test method to verify ST ESD advanced protection on RS-232 or RS485 I/O device.

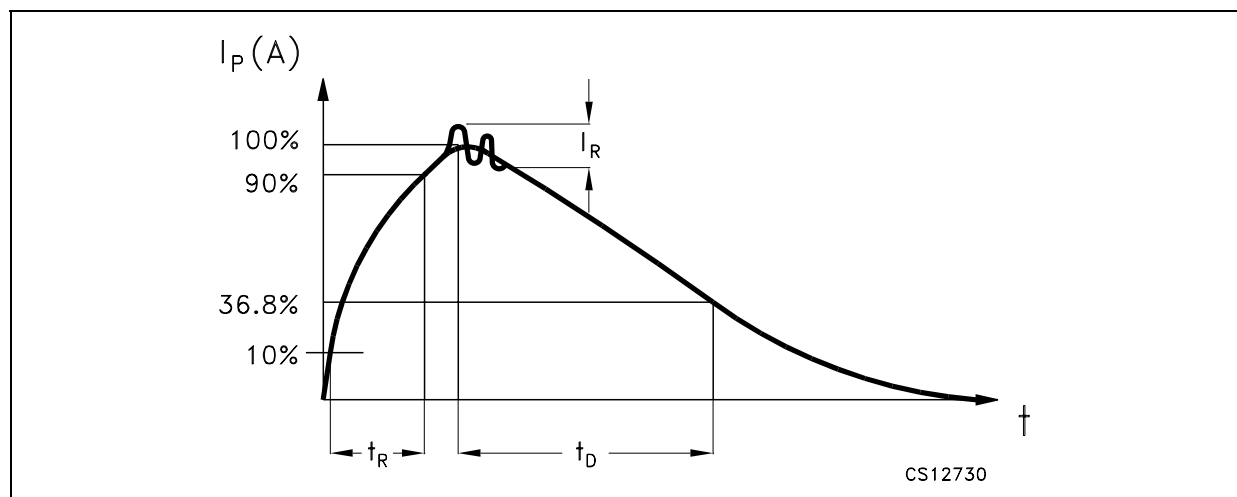
Static electricity is defined as an electrical charge caused by an imbalance of electrons on the surface of a material. This imbalance of electrons produces an electric field that can be measured and that can influence other objects at a distance. Electrostatic discharge is defined as the transfer of charge between bodies at different electrical potentials. Electrostatic discharge (ESD) can change the electrical characteristics of a semiconductor device, degrading or destroying it. Any input or output port (I/O) allows access communication with other pieces of equipment by external connectors. These connectors are directly linked by the I/O pins of RS-232 or RS485 interface. ST provides the E-series by advanced high ESD protection structure. The protection functionality is tested in two different conditions:

The first model is used to simulate the HUMAN BODY MODEL (HBM) event. A similar discharge can occur from a charged conductive object, such as a metallic tool or fixture. The model used to characterize this event is known as the Machine Model. A Human Body Model circuit and waveform is presented in Figures below.

HUMAN BODY MODEL CIRCUIT

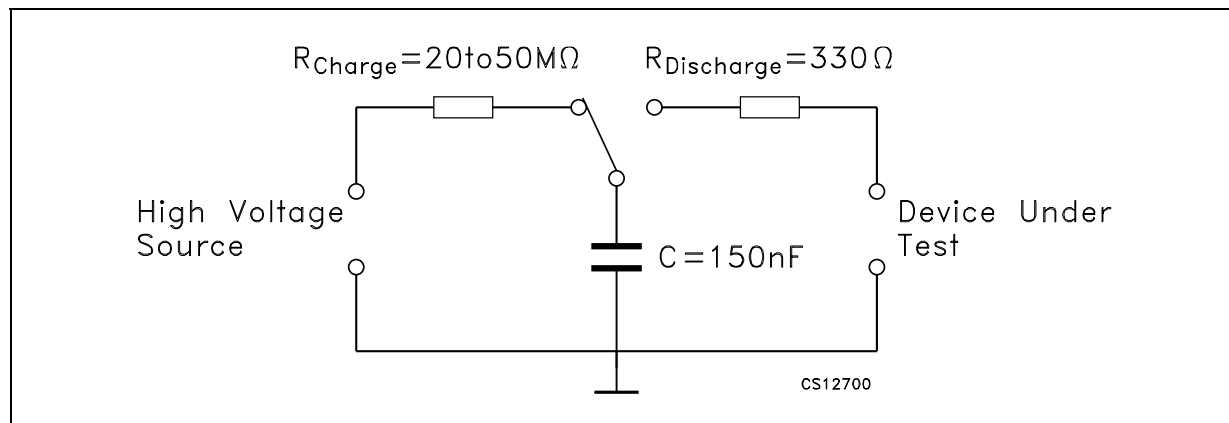


HUMAN BODY MODEL CURRENT WAVEFORM

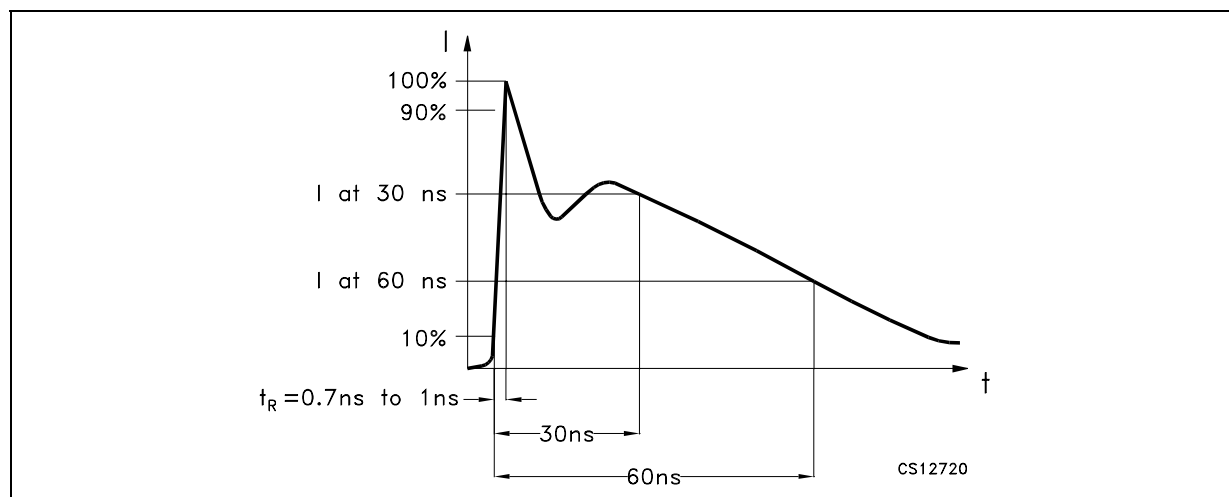


The second model is IEC 1000-4-2 and is used to simulate the reaction of the device on equipment when subjected to electrostatic discharges, which may occur from personnel to objects near vital instrumentation. Direct (Contact) and indirect (Air Gap) applications of discharges to the equipment under test (EUT) are possible. Test characteristics are shown in circuit, waveform and table below.

IEC 1000-4-2 CIRCUIT



IEC 1000-4-2 CURRENT WAVEFORM

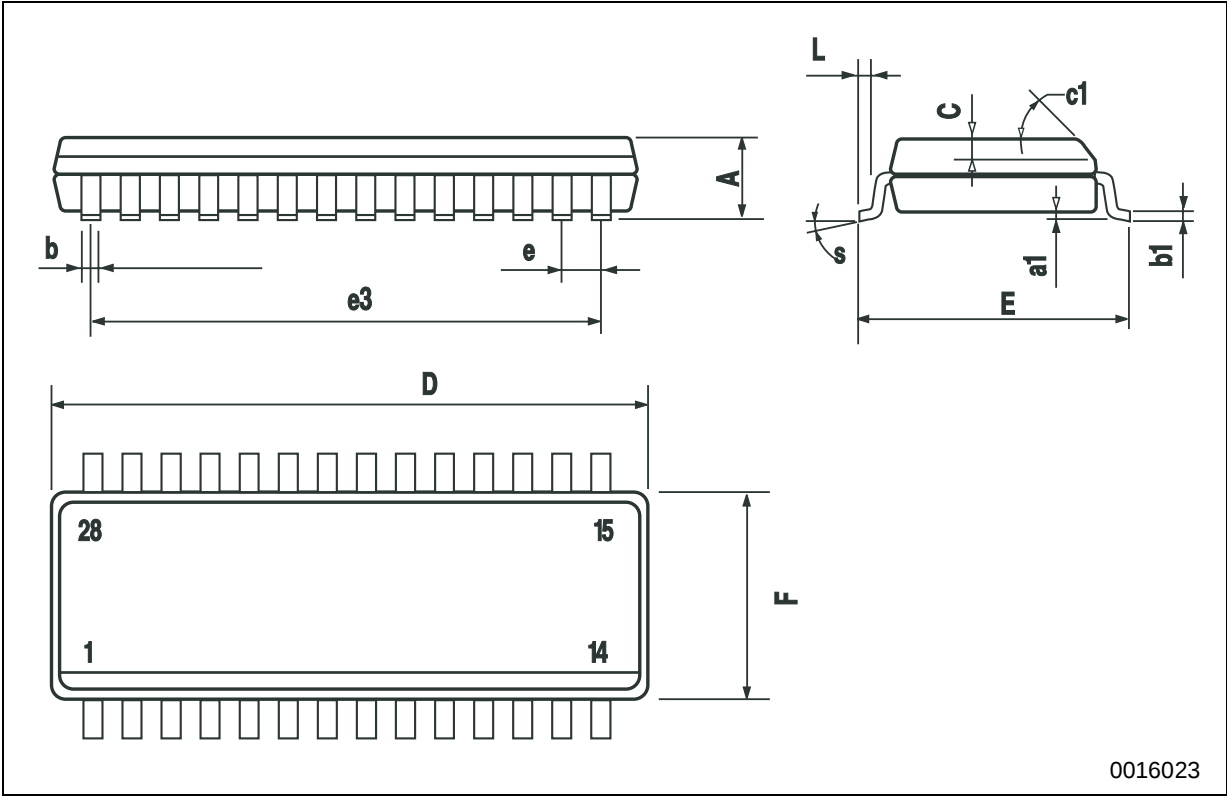


CHARACTERISTICS OF THE ESD GENERATOR

Level	Indicated Voltage	First Peak Current of Discharge ($\pm 10\%$)	Rise Time With Discharge Switch	Current at 30 ns ($\pm 30\%$)	Current at 60 ns ($\pm 30\%$)
1	2 KV	7.5 A	0.7 to 1ns	4 A	2 A
2	4 KV	15 A	0.7 to 1ns	8 A	4 A
3	6 KV	22.5 A	0.7 to 1ns	12 A	6 A
4	8 KV	30 A	0.7 to 1ns	16 A	8 A

SO-28 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			2.65			0.104
a1	0.1		0.3	0.004		0.012
b	0.35		0.49	0.014		0.019
b1	0.23		0.32	0.009		0.012
C		0.5			0.020	
c1	45° (typ.)					
D	17.70		18.10	0.697		0.713
E	10.00		10.65	0.393		0.419
e		1.27			0.050	
e3		16.51			0.650	
F	7.40		7.60	0.291		0.300
L	0.50		1.27	0.020		0.050
S	8° (max.)					

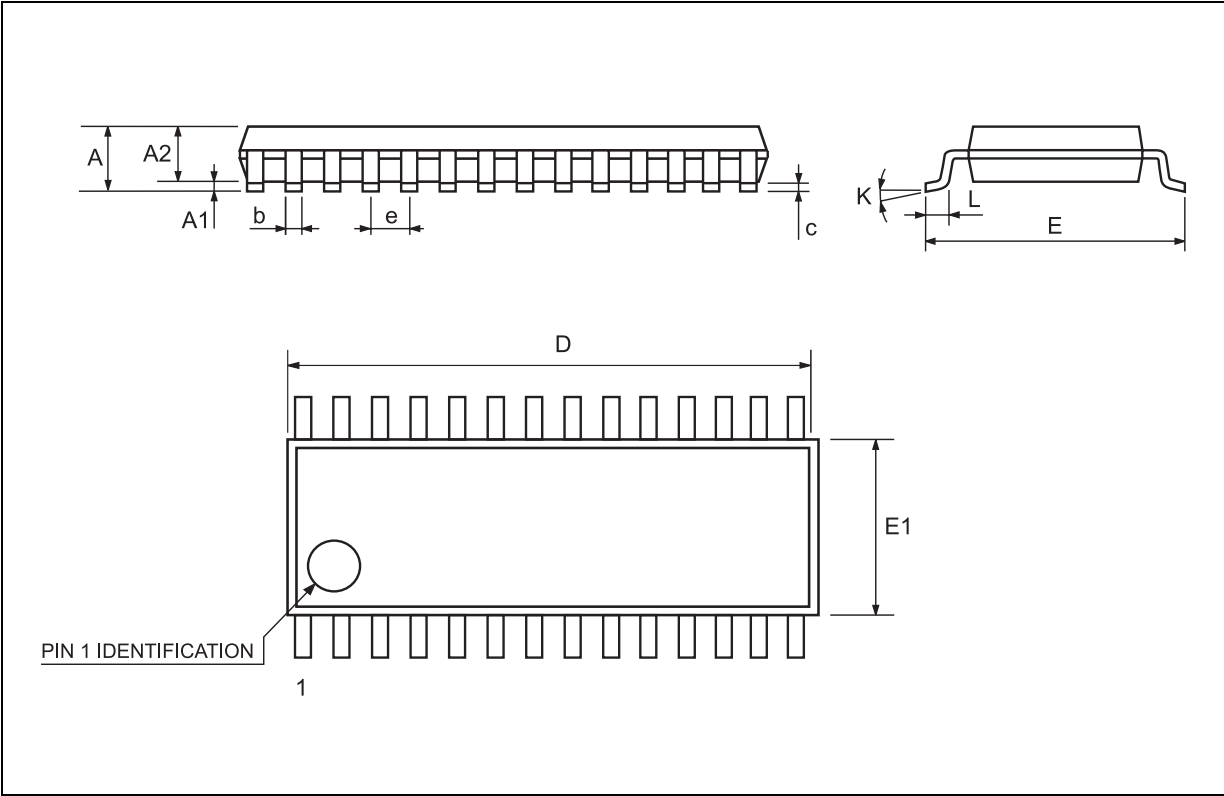


0016023



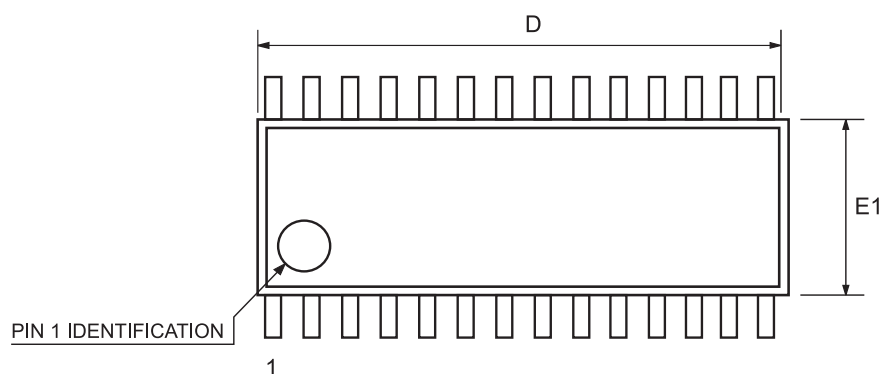
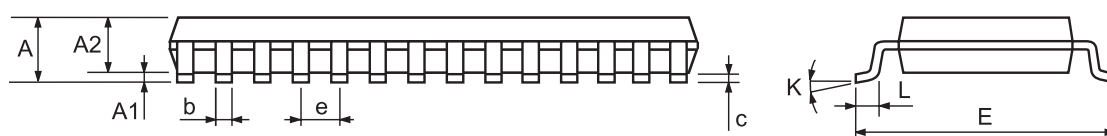
SSOP28 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			2			0.079
A1	0.050			0.002		
A2	1.65	1.75	1.85	0.065	0.069	0.073
b	0.22		0.38	0.009		0.015
c	0.09		0.25	0.004		0.010
D	9.9	10.2	10.5	0.390	0.402	0.413
E	7.4	7.8	8.2	0.291	0.307	0.323
E1	5	5.3	5.6	0.197	0.209	0.220
e		0.65 BSC			0.0256 BSC	
K	0°		10°	0°		10°
L	0.55	0.75	0.95	0.022	0.030	0.037



TSSOP28 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0079
D	9.6	9.7	9.8	0.378	0.382	0.386
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



0128292B

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

© The ST logo is a registered trademark of STMicroelectronics

© 2003 STMicroelectronics - Printed in Italy - All Rights Reserved
STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco
Singapore - Spain - Sweden - Switzerland - United Kingdom - United States.

© <http://www.st.com>

